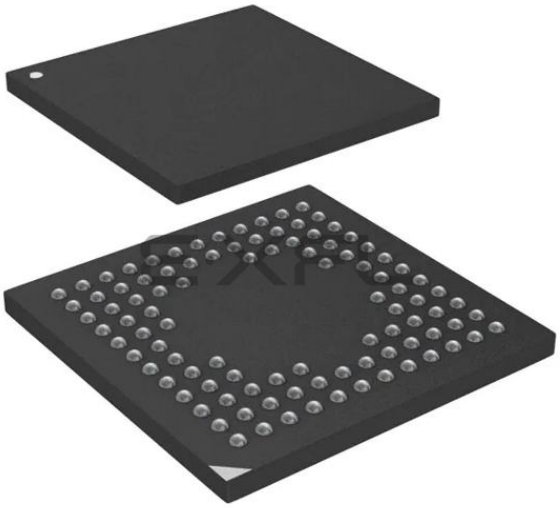


Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, Motor Control PWM, PDR, POR, PVD, PWM, Temp Sensor, WDT
Number of I/O	80
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 16x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-UFBGA
Supplier Device Package	100-UFBGA (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f103vbi6

Contents

1 Introduction 9

2 Description 9

2.1 Device overview 10

2.2 Full compatibility throughout the family 13

2.3 Overview 14

2.3.1 ARM® Cortex®-M3 core with embedded Flash and SRAM 14

2.3.2 Embedded Flash memory 14

2.3.3 CRC (cyclic redundancy check) calculation unit 14

2.3.4 Embedded SRAM 14

2.3.5 Nested vectored interrupt controller (NVIC) 14

2.3.6 External interrupt/event controller (EXTI) 15

2.3.7 Clocks and startup 15

2.3.8 Boot modes 15

2.3.9 Power supply schemes 15

2.3.10 Power supply supervisor 15

2.3.11 Voltage regulator 16

2.3.12 Low-power modes 16

2.3.13 DMA 17

2.3.14 RTC (real-time clock) and backup registers 17

2.3.15 Timers and watchdogs 17

2.3.16 I²C bus 19

2.3.17 Universal synchronous/asynchronous receiver transmitter (USART) . . 19

2.3.18 Serial peripheral interface (SPI) 19

2.3.19 Controller area network (CAN) 19

2.3.20 Universal serial bus (USB) 19

2.3.21 GPIOs (general-purpose inputs/outputs) 20

2.3.22 ADC (analog-to-digital converter) 20

2.3.23 Temperature sensor 20

2.3.24 Serial wire JTAG debug port (SWJ-DP) 20

3 Pinouts and pin description 21

4 Memory mapping 34

This hardware block provides flexible interrupt management features with minimal interrupt latency.

2.3.6 External interrupt/event controller (EXTI)

The external interrupt/event controller consists of 19 edge detector lines used to generate interrupt/event requests. Each line can be independently configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 80 GPIOs can be connected to the 16 external interrupt lines.

2.3.7 Clocks and startup

System clock selection is performed on startup, however the internal RC 8 MHz oscillator is selected as default CPU clock on reset. An external 4-16 MHz clock can be selected, in which case it is monitored for failure. If failure is detected, the system automatically switches back to the internal RC oscillator. A software interrupt is generated if enabled. Similarly, full interrupt management of the PLL clock entry is available when necessary (for example on failure of an indirectly used external crystal, resonator or oscillator).

Several prescalers allow the configuration of the AHB frequency, the high-speed APB (APB2) and the low-speed APB (APB1) domains. The maximum frequency of the AHB and the high-speed APB domains is 72 MHz. The maximum allowed frequency of the low-speed APB domain is 36 MHz. See *Figure 2* for details on the clock tree.

2.3.8 Boot modes

At startup, boot pins are used to select one of three boot options:

- Boot from User Flash
- Boot from System Memory
- Boot from embedded SRAM

The boot loader is located in System Memory. It is used to reprogram the Flash memory by using USART1. For further details please refer to AN2606.

2.3.9 Power supply schemes

- V_{DD} = 2.0 to 3.6 V: external power supply for I/Os and the internal regulator. Provided externally through V_{DD} pins.
- V_{SSA}, V_{DDA} = 2.0 to 3.6 V: external analog power supplies for ADC, reset blocks, RCs and PLL (minimum voltage to be applied to V_{DDA} is 2.4 V when the ADC is used). V_{DDA} and V_{SSA} must be connected to V_{DD} and V_{SS}, respectively.
- V_{BAT} = 1.8 to 3.6 V: power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when V_{DD} is not present.

For more details on how to connect power pins, refer to *Figure 14: Power supply scheme*.

2.3.10 Power supply supervisor

The device has an integrated power-on reset (POR)/power-down reset (PDR) circuitry. It is always active, and ensures proper operation starting from/down to 2 V. The device remains

5 Electrical characteristics

5.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

5.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A = 25 °C and T_A = $T_A$max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean±3σ).

5.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = 3.3 V (for the 2 V ≤ V_{DD} ≤ 3.6 V voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean±2σ).

5.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

5.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 12*.

5.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 13*.

Figure 12. Pin loading conditions

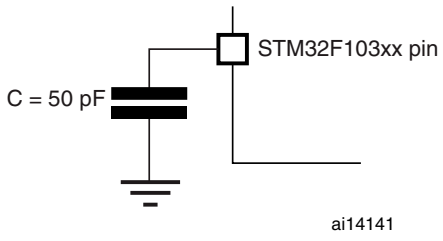
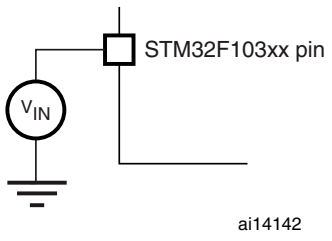
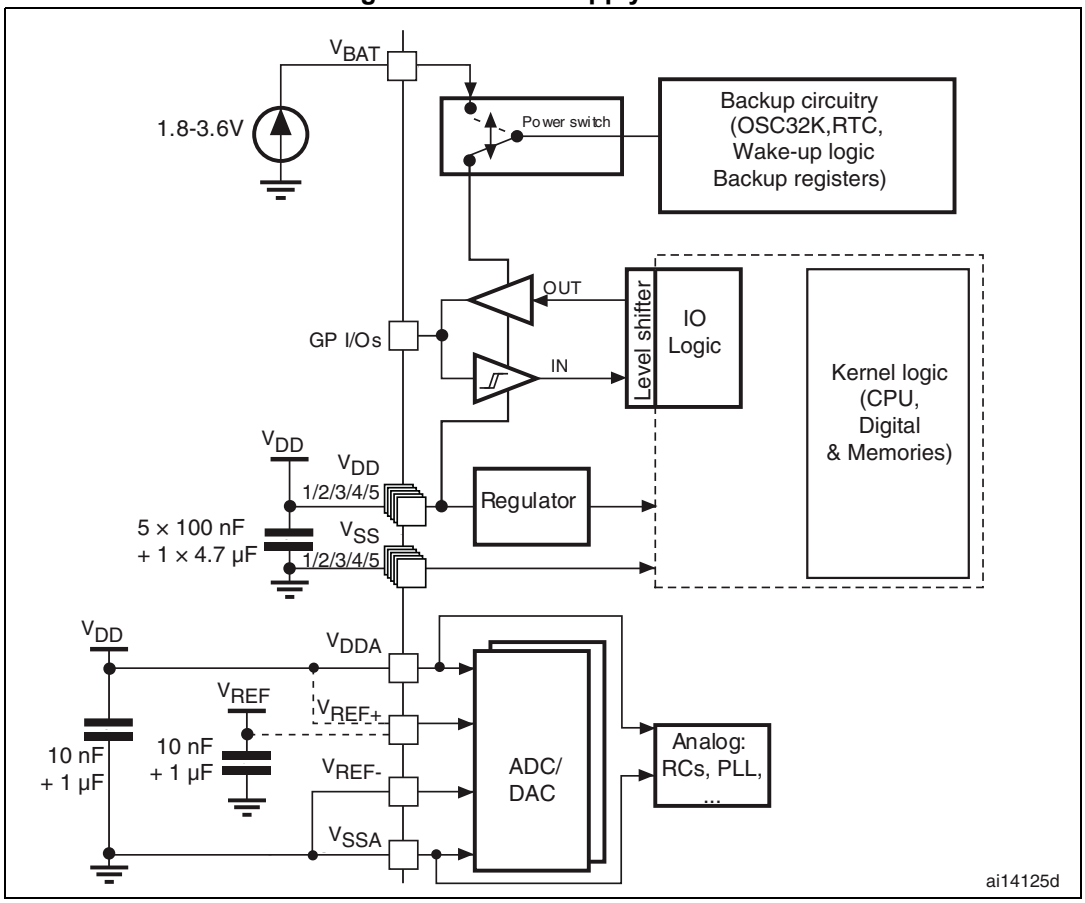


Figure 13. Pin input voltage



5.1.6 Power supply scheme

Figure 14. Power supply scheme



Caution: In *Figure 14*, the 4.7 µF capacitor must be connected to V_{DD3}.

5.1.7 Current consumption measurement

Figure 15. Current consumption measurement scheme

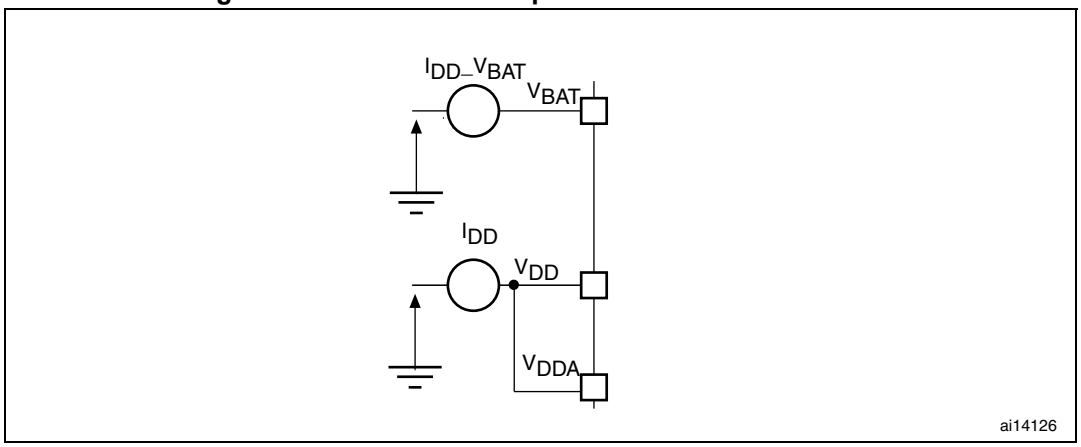


Table 8. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	–65 to +150	°C
T_J	Maximum junction temperature	150	°C

5.3 Operating conditions

5.3.1 General operating conditions

Table 9. General operating conditions

Symbol	Parameter	Conditions		Min	Max	Unit
f_{HCLK}	Internal AHB clock frequency	-		0	72	MHz
f_{PCLK1}	Internal APB1 clock frequency	-		0	36	
f_{PCLK2}	Internal APB2 clock frequency	-		0	72	
V_{DD}	Standard operating voltage	-		2	3.6	V
V_{DDA}(1)	Analog operating voltage (ADC not used)	Must be the same potential as V_{DD}(2)		2	3.6	
	Analog operating voltage (ADC used)			2.4	3.6	
V_{BAT}	Backup operating voltage	-		1.8	3.6	
V_{IN}	I/O input voltage	Standard IO		–0.3	V_{DD}+ 0.3	V
		FT IO(3)	2 V < V_{DD} ≤ 3.6 V	–0.3	5.5	
			V_{DD} = 2 V	–0.3	5.2	
		BOOT0		0	5.5	
P_D	Power dissipation at T_A = 85 °C for suffix 6 or T_A = 105 °C for suffix 7(4)	LFBGA100		-	454	mW
		LQFP100		-	434	
		UFBGA100		-	339	
		TFBGA64		-	308	
		LQFP64		-	444	
		LQFP48		-	363	
		UFQFPN48		-	624	
		VFQFPN36		-	1000	

5.3.3 Embedded reset and power control block characteristics

The parameters given in *Table 11* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 9*.

Table 11. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{PVD}	Programmable voltage detector level selection	PLS[2:0]=000 (rising edge)	2.1	2.18	2.26	V
		PLS[2:0]=000 (falling edge)	2	2.08	2.16	
		PLS[2:0]=001 (rising edge)	2.19	2.28	2.37	
		PLS[2:0]=001 (falling edge)	2.09	2.18	2.27	
		PLS[2:0]=010 (rising edge)	2.28	2.38	2.48	
		PLS[2:0]=010 (falling edge)	2.18	2.28	2.38	
		PLS[2:0]=011 (rising edge)	2.38	2.48	2.58	
		PLS[2:0]=011 (falling edge)	2.28	2.38	2.48	
		PLS[2:0]=100 (rising edge)	2.47	2.58	2.69	
		PLS[2:0]=100 (falling edge)	2.37	2.48	2.59	
		PLS[2:0]=101 (rising edge)	2.57	2.68	2.79	
		PLS[2:0]=101 (falling edge)	2.47	2.58	2.69	
		PLS[2:0]=110 (rising edge)	2.66	2.78	2.9	
		PLS[2:0]=110 (falling edge)	2.56	2.68	2.8	
		PLS[2:0]=111 (rising edge)	2.76	2.88	3	
		PLS[2:0]=111 (falling edge)	2.66	2.78	2.9	
$V_{PVDhyst}$(2)	PVD hysteresis	-	-	100	-	mV
$V_{POR/PDR}$	Power on/power down reset threshold	Falling edge	1.8(1)	1.88	1.96	V
		Rising edge	1.84	1.92	2.0	
$V_{PDRhyst}$(2)	PDR hysteresis	-	-	40	-	mV
$T_{RSTTEMPO}$(2)	Reset temporization	-	1	2.5	4.5	ms

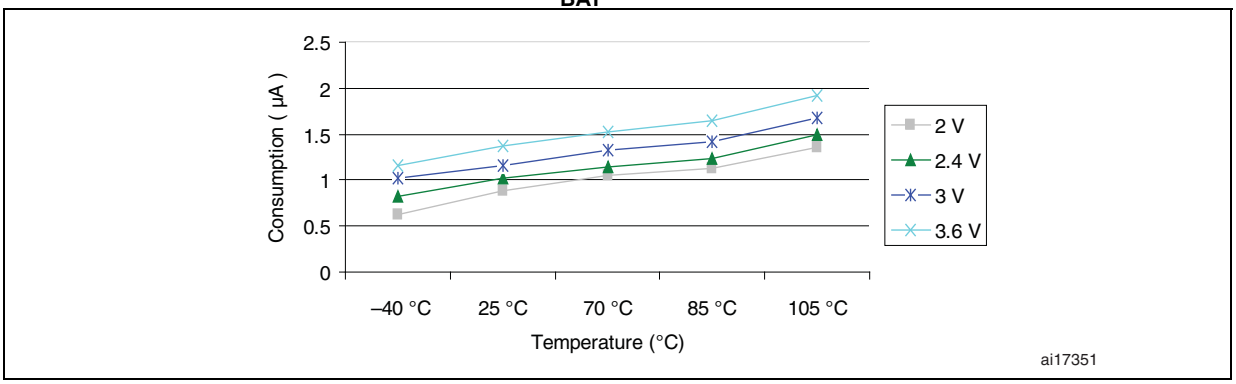
1. The product behavior is guaranteed by design down to the minimum $V_{POR/PDR}$ value.
2. Guaranteed by design.

Table 16. Typical and maximum current consumptions in Stop and Standby modes

Symbol	Parameter	Conditions	Typ(1)			Max		Unit
			V_{DD}/V_{BAT} = 2.0 V	V_{DD}/V_{BAT} = 2.4 V	V_{DD}/V_{BAT} = 3.3 V	T_A = 85 °C	T_A = 105 °C	
I_{DD}	Supply current in Stop mode	Regulator in Run mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	-	23.5	24	200	370	µA
		Regulator in Low-power mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	-	13.5	14	180	340	
	Supply current in Standby mode	Low-speed internal RC oscillator and independent watchdog ON	-	2.6	3.4	-	-	
		Low-speed internal RC oscillator ON, independent watchdog OFF	-	2.4	3.2	-	-	
		Low-speed internal RC oscillator and independent watchdog OFF, low-speed oscillator and RTC OFF	-	1.7	2	4	5	
I_{DD_VBAT}	Backup domain supply current	Low-speed oscillator and RTC ON	0.9	1.1	1.4	1.9(2)	2.2	

1. Typical values are measured at T_A = 25 °C.
2. Guaranteed based on test during characterization.

Figure 18. Typical current consumption on V_{BAT} with RTC on versus temperature at different V_{BAT} values



On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in *Table 19*. The MCU is placed under the following conditions:

- all I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
  - with all peripherals clocked off
  - with only one peripheral clocked on
- ambient operating temperature and V_{DD} supply voltage conditions summarized in *Table 6*

Table 19. Peripheral current consumption

Peripherals		µA/MHz
AHB (up to 72 MHz)	DMA1	16.53
	BusMatrix(1)	8.33
APB1 (up to 36 MHz)	APB1-Bridge	10.28
	TIM2	32.50
	TIM3	31.39
	TIM4	31.94
	SPI2	4.17
	USART2	12.22
	USART3	12.22
	I2C1	10.00
	I2C2	10.00
	USB	17.78
	CAN1	18.06
	WWDG	2.50
	PWR	1.67
	BKP	2.50
	IWDG	11.67

Table 23. LSE oscillator characteristics (f_{LSE} = 32.768 kHz)(1) (2) (continued)

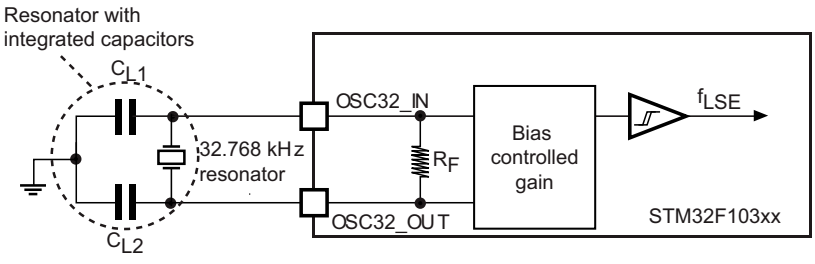
Symbol	Parameter	Conditions	-	Min	Typ	Max	Unit
$t_{SU(LSE)}$(3)	Startup time	V_{DD} is stabilized	T_A = 50 °C	-	1.5	-	s
			T_A = 25 °C	-	2.5	-	
			T_A = 10 °C	-	4	-	
			T_A = 0 °C	-	6	-	
			T_A = -10 °C	-	10	-	
			T_A = -20 °C	-	17	-	
			T_A = -30 °C	-	32	-	
			T_A = -40 °C	-	60	-	

1. Guaranteed based on test during characterization.
2. Refer to the note and caution paragraphs below the table, and to the application note AN2867 “Oscillator design guide for ST microcontrollers”.
3. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal and it can vary significantly with the crystal manufacturer

Note: For C_{L1} and C_{L2} it is recommended to use high-quality ceramic capacitors in the 5 pF to 15 pF range selected to match the requirements of the crystal or resonator. C_{L1} and C_{L2}, are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}.
Load capacitance C_L has the following formula: $C_L = C_{L1} \times C_{L2} / (C_{L1} + C_{L2}) + C_{stray}$ where C_{stray} is the pin capacitance and board or trace PCB-related capacitance. Typically, it is between 2 pF and 7 pF.

Caution: To avoid exceeding the maximum value of C_{L1} and C_{L2} (15 pF) it is strongly recommended to use a resonator with a load capacitance $C_L \leq 7$ pF. Never use a resonator with a load capacitance of 12.5 pF.
Example: if you choose a resonator with a load capacitance of C_L = 6 pF, and C_{stray} = 2 pF, then $C_{L1} = C_{L2}$ = 8 pF.

Figure 25. Typical application with a 32.768 kHz crystal



5.3.7 Internal clock source characteristics

The parameters given in *Table 24* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 9*.

Table 26. Low-power mode wakeup timings

Symbol	Parameter	Typ	Unit
$t_{WUSLEEP}$(1)	Wakeup from Sleep mode	1.8	µs
t_{WUSTOP}(1)	Wakeup from Stop mode (regulator in run mode)	3.6	
	Wakeup from Stop mode (regulator in low-power mode)	5.4	
$t_{WUSTDBY}$(1)	Wakeup from Standby mode	50	

1. The wakeup times are measured from the wakeup event to the point in which the user application code reads the first instruction.

5.3.8 PLL characteristics

The parameters given in *Table 27* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 9*.

Table 27. PLL characteristics

Symbol	Parameter	Value			Unit
		Min(1)	Typ	Max(1)	
f_{PLL_IN}	PLL input clock(2)	1	8.0	25	MHz
	PLL input clock duty cycle	40	-	60	%
f_{PLL_OUT}	PLL multiplier output clock	16	-	72	MHz
t_{LOCK}	PLL lock time	-	-	200	µs
Jitter	Cycle-to-cycle jitter	-	-	300	ps

1. Guaranteed based on test during characterization.
2. Take care of using the appropriate multiplier factors so as to have PLL input clock values compatible with the range defined by f_{PLL_OUT}.

5.3.9 Memory characteristics

Flash memory

The characteristics are given at T_A = –40 to 105 °C unless otherwise specified.

Table 28. Flash memory characteristics

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
t_{prog}	16-bit programming time	T_A = –40 to +105 °C	40	52.5	70	µs
t_{ERASE}	Page (1 KB) erase time	T_A = –40 to +105 °C	20	-	40	ms
t_{ME}	Mass erase time	T_A = –40 to +105 °C	20	-	40	

Table 28. Flash memory characteristics (continued)

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
I_{DD}	Supply current	Read mode f_{HCLK} = 72 MHz with 2 wait states, V_{DD} = 3.3 V	-	-	20	mA
		Write / Erase modes f_{HCLK} = 72 MHz, V_{DD} = 3.3 V	-	-	5	
		Power-down mode / Halt, V_{DD} = 3.0 to 3.6 V	-	-	50	µA
V_{prog}	Programming voltage	-	2	-	3.6	V

1. Guaranteed by design.

Table 29. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Value			Unit
			Min(1)	Typ	Max	
N_{END}	Endurance	T_A = –40 to +85 °C (6 suffix versions) T_A = –40 to +105 °C (7 suffix versions)	10	-	-	kcycles
t_{RET}	Data retention	1 kcycle(2) at T_A = 85 °C	30	-	-	Years
		1 kcycle(2) at T_A = 105 °C	10	-	-	
		10 kcycles(2) at T_A = 55 °C	20	-	-	

1. Guaranteed based on test during characterization.
2. Cycling performed over the whole temperature range.

5.3.10 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 30*. They are based on the EMS levels and classes defined in application note AN1709.

5.3.16 Communications interfaces

I²C interface characteristics

The STM32F103xx performance line I²C interface meets the requirements of the standard I²C communication protocol with the following restrictions: the I/O pins SDA and SCL are mapped to are not “true” open-drain. When configured as open-drain, the PMOS connected between the I/O pin and V_{DD} is disabled, but is still present.

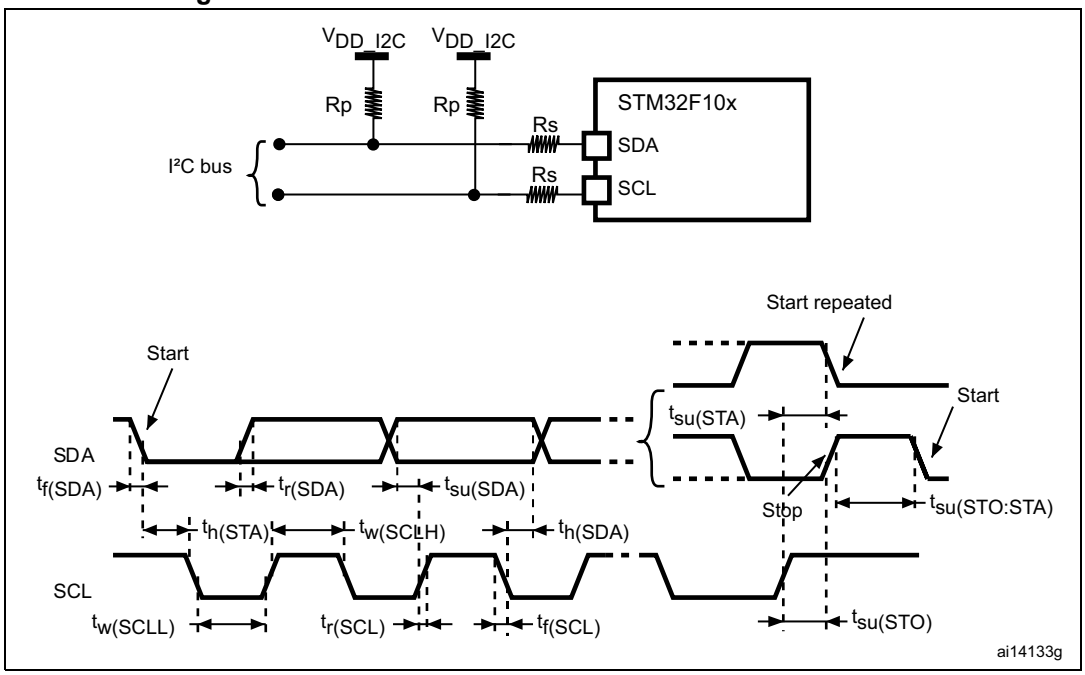
The I²C characteristics are described in *Table 40*. Refer also to *Section 5.3.12: I/O current injection characteristics* for more details on the input/output alternate function characteristics (SDA and SCL).

Table 40. I²C characteristics

Symbol	Parameter	Standard mode I²C(1)(2)		Fast mode I²C(1)(2)		Unit
		Min	Max	Min	Max	
$t_{w(SCLL)}$	SCL clock low time	4.7	-	1.3	-	µs
$t_{w(SCLH)}$	SCL clock high time	4.0	-	0.6		
$t_{su(SDA)}$	SDA setup time	250	-	100	-	ns
$t_{h(SDA)}$	SDA data hold time	-	3450(3)	-	900(3)	
$t_{r(SDA)}$ $t_{r(SCL)}$	SDA and SCL rise time	-	1000	-	300	
$t_{f(SDA)}$ $t_{f(SCL)}$	SDA and SCL fall time	-	300	-	300	
$t_{h(STA)}$	Start condition hold time	4.0	-	0.6	-	µs
$t_{su(STA)}$	Repeated Start condition setup time	4.7	-	0.6	-	
$t_{su(STO)}$	Stop condition setup time	4.0	-	0.6	-	µs
$t_{w(STO:STA)}$	Stop to Start condition time (bus free)	4.7	-	1.3	-	µs
C_b	Capacitive load for each bus line	-	400	-	400	pF
t_{SP}	Pulse width of spikes that are suppressed by the analog filter	0	50(4)	0	50(4)	ns

1. Guaranteed by design.
2. f_{PCLK1} must be at least 2 MHz to achieve standard mode I²C frequencies. It must be at least 4 MHz to achieve fast mode I²C frequencies. It must be a multiple of 10 MHz to reach the 400 kHz maximum I2C fast mode clock.
3. The maximum Data hold time has only to be met if the interface does not stretch the low period of SCL signal.
4. The minimum width of the spikes filtered by the analog filter is above t_{SP}(max).

Figure 32. I²C bus AC waveforms and measurement circuit



1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.
2. Rs = Series protection resistors, Rp = Pull-up resistors, V_{DD_I2C} = I2C bus supply.

Table 41. SCL frequency (f_{PCLK1}= 36 MHz.,V_{DD_I2C} = 3.3 V)(1)(2)

f_{SCL} (kHz)	I2C_CCR value
	R_P = 4.7 kΩ
400	0x801E
300	0x8028
200	0x803C
100	0x00B4
50	0x0168
20	0x0384

1. R_P = External pull-up resistance, f_{SCL} = I²C speed,
2. For speeds around 200 kHz, the tolerance on the achieved speed is of ±5%. For other speed ranges, the tolerance on the achieved speed ±2%. These variations depend on the accuracy of the external components used to design the application.

Figure 33. SPI timing diagram - slave mode and CPHA = 0

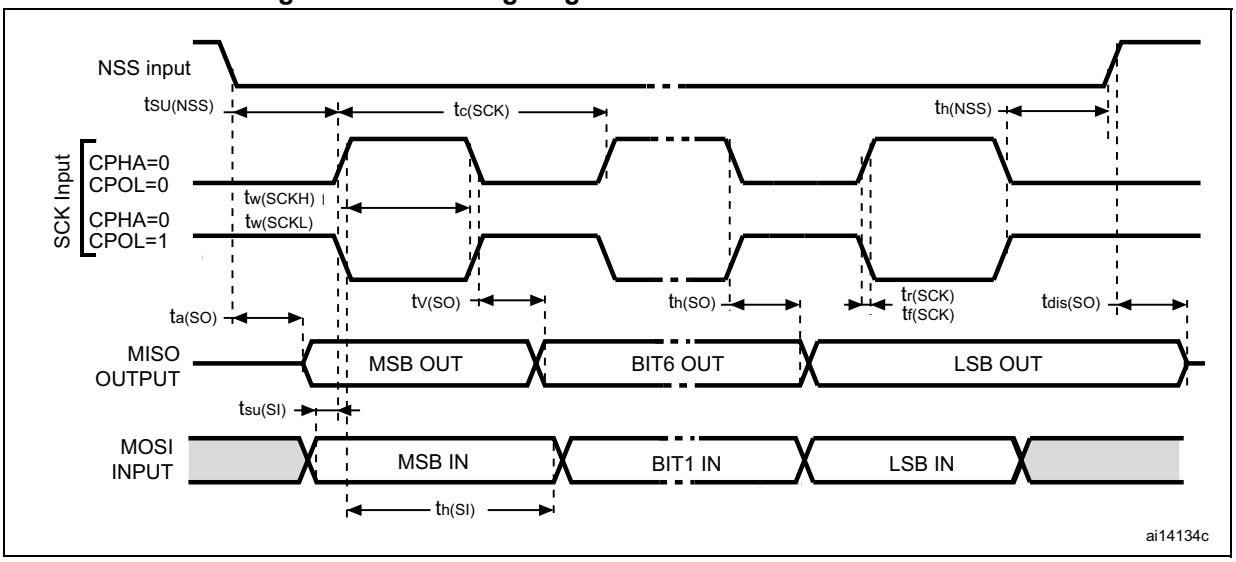
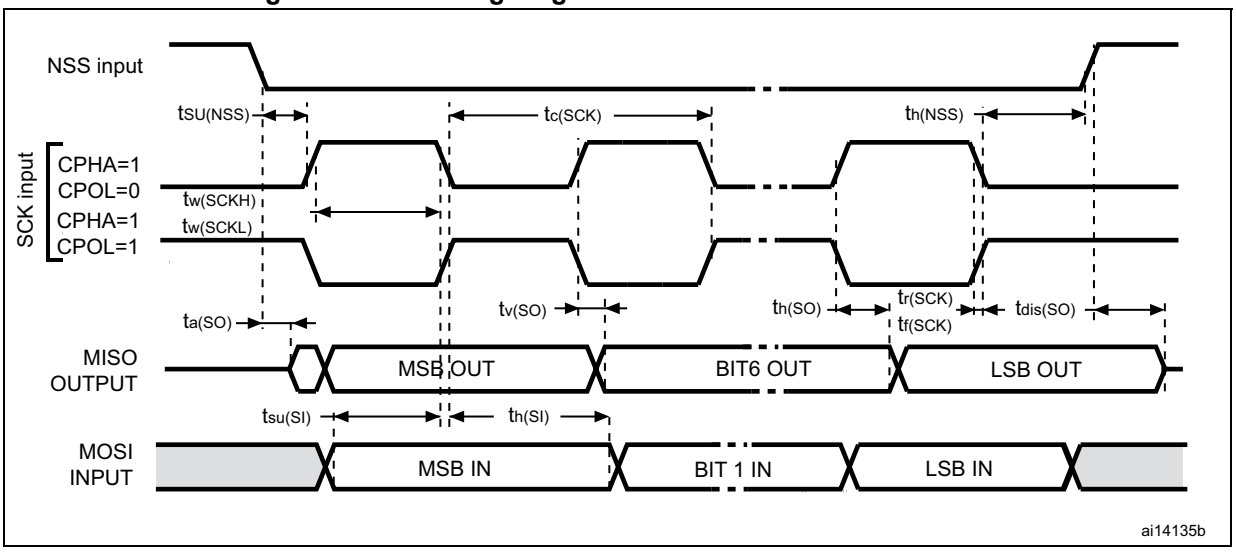


Figure 34. SPI timing diagram - slave mode and CPHA = 1(1)



1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

5.3.18 12-bit ADC characteristics

Unless otherwise specified, the parameters given in *Table 46* are derived from tests performed under the ambient temperature, f_{PCLK2} frequency and V_{DDA} supply voltage conditions summarized in *Table 9*.

Note: It is recommended to perform a calibration after each power-up.

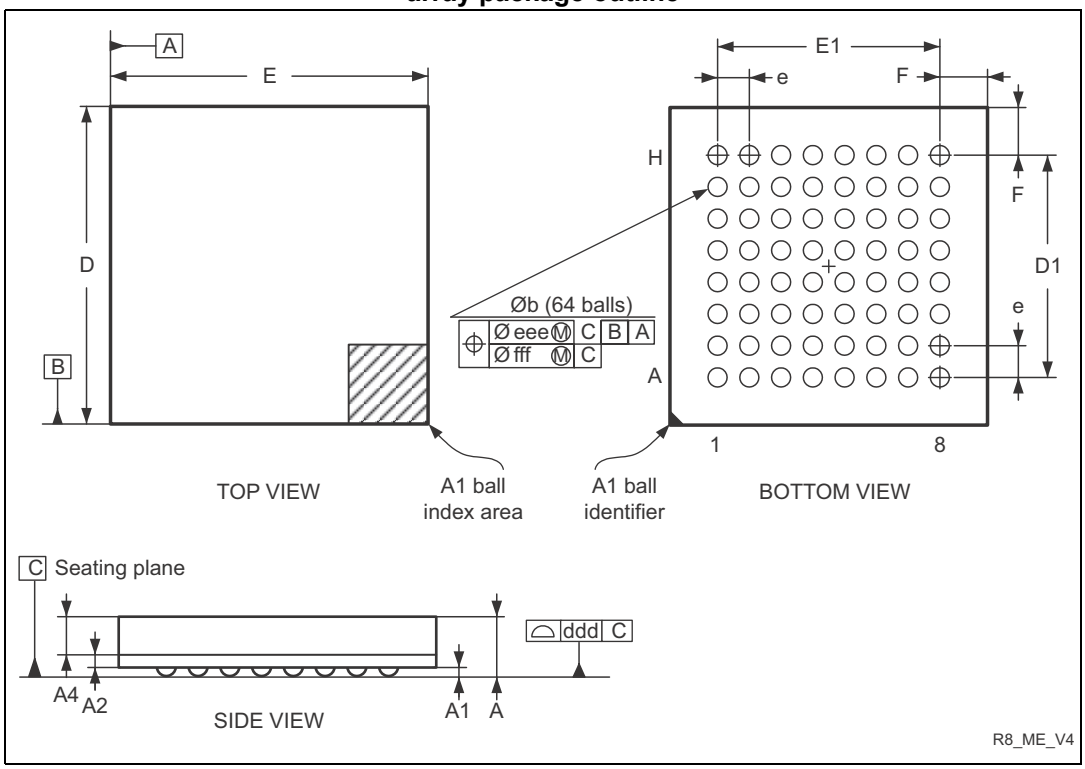
Table 46. ADC characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Power supply	-	2.4	-	3.6	V
V_{REF+}	Positive reference voltage	-	2.4	-	V_{DDA}	V
I_{VREF}	Current on the V_{REF} input pin	-	-	160(1)	220(1)	µA
f_{ADC}	ADC clock frequency	-	0.6	-	14	MHz
f_S(2)	Sampling rate	-	0.05	-	1	MHz
f_{TRIG}(2)	External trigger frequency	f_{ADC} = 14 MHz	-	-	823	kHz
			-	-	17	$1/f_{ADC}$
V_{AIN}(3)	Conversion voltage range		0 (V_{SSA} or V_{REF-} tied to ground)	-	V_{REF+}	V
R_{AIN}(2)	External input impedance	See *Equation 1* and *Table 47* for details	-	-	50	kΩ
R_{ADC}(2)	Sampling switch resistance	-	-	-	1	kΩ
C_{ADC}(2)	Internal sample and hold capacitor	-	-	-	8	pF
t_{CAL}(2)	Calibration time	f_{ADC} = 14 MHz	5.9			µs
		-	83			$1/f_{ADC}$
t_{lat}(2)	Injection trigger conversion latency	f_{ADC} = 14 MHz	-	-	0.214	µs
		-	-	-	3(4)	$1/f_{ADC}$
t_{latr}(2)	Regular trigger conversion latency	f_{ADC} = 14 MHz	-	-	0.143	µs
		-	-	-	2(4)	$1/f_{ADC}$
t_S(2)	Sampling time	f_{ADC} = 14 MHz	0.107	-	17.1	µs
		-	1.5	-	239.5	$1/f_{ADC}$
t_{STAB}(2)	Power-up time	-	0	0	1	µs
t_{CONV}(2)	Total conversion time (including sampling time)	f_{ADC} = 14 MHz	1	-	18	µs
		-	14 to 252 (t_S for sampling +12.5 for successive approximation)			$1/f_{ADC}$

1. Guaranteed based on test during characterization.
2. Guaranteed by design.
3. In devices delivered in VFQFPN and LQFP packages, V_{REF+} is internally connected to V_{DDA} and V_{REF-} is internally connected to V_{SSA}. Devices that come in the TFBGA64 package have a V_{REF+} pin but no V_{REF-} pin (V_{REF-} is internally connected to V_{SSA}), see *Table 5* and *Figure 7*.
4. For external triggers, a delay of $1/f_{PCLK2}$ must be added to the latency specified in *Table 46*.

6.7 TFBGA64 5 x 5 mm, thin profile fine pitch package information

Figure 59. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch thin profile fine pitch ball grid array package outline



1. Drawing is not to scale.

Table 59. TFBGA64 – 64-ball, 5 x 5 mm, 0.5 mm pitch, thin profile fine pitch ball grid array package mechanical data

Symbol	millimeters			inches(1)		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.200	-	-	0.0472
A1	0.150	-	-	0.0059	-	-
A2	-	0.200	-	-	0.0079	-
A4	-	-	0.600	-	-	0.0236
b	0.250	0.300	0.350	0.0098	0.0118	0.0138
D	4.850	5.000	5.150	0.1909	0.1969	0.2028
D1	-	3.500	-	-	0.1378	-
E	4.850	5.000	5.150	0.1909	0.1969	0.2028
E1	-	3.500	-	-	0.1378	-
e	-	0.500	-	-	0.0197	-
F	-	0.750	-	-	0.0295	-

Using the values obtained in *Table 62* T_{Jmax} is calculated as follows:

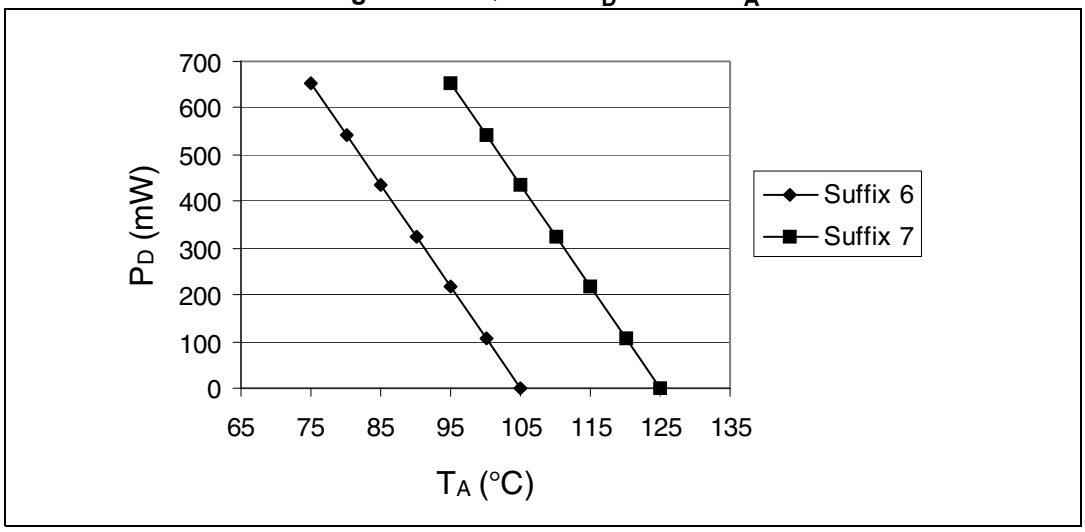
– For LQFP100, 46 °C/W

T_{Jmax} = 115 °C + (46 °C/W × 134 mW) = 115 °C + 6.2 °C = 121.2 °C

This is within the range of the suffix 7 version parts (–40 < T_J < 125 °C).

In this case, parts must be ordered at least with the temperature range suffix 7 (see *Table 63: Ordering information scheme*).

Figure 65. LQFP100 P_D max vs. T_A



7 Ordering information scheme

Table 63. Ordering information scheme

Example: STM32 F 103 C 8 T 7 xxx

Device family

STM32 = ARM-based 32-bit microcontroller

Product type

F = general-purpose

Device subfamily

103 = performance line

Pin count

T = 36 pins
C = 48 pins
R = 64 pins
V = 100 pins

Flash memory size

8 = 64 Kbytes of Flash memory
B = 128 Kbytes of Flash memory

Package

H = BGA
I = UFBGA
T = LQFP
U = VFQFPN or UFQFPN

Temperature range

6 = Industrial temperature range, –40 to 85 °C.
7 = Industrial temperature range, –40 to 105 °C.

Options

xxx = programmed parts
TR = tape and real

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.

Table 64. Document revision history (continued)

Date	Revision	Changes
14-Mar-2008	5	*Figure 2: Clock tree on page 12* added. Maximum T_J value given in *Table 8: Thermal characteristics on page 38*. CRC feature added (see *CRC (cyclic redundancy check) calculation unit on page 9* and *Figure 11: Memory map on page 34* for address). I_{DD} modified in *Table 16: Typical and maximum current consumptions in Stop and Standby modes*. ACC_{HSI} modified in *Table 24: HSI oscillator characteristics on page 56*, note 2 removed. P_D, T_A and T_J added, t_{prog} values modified and t_{prog} description clarified in *Table 28: Flash memory characteristics on page 57*. t_{RET} modified in *Table :* . $V_{NF(NRST)}$ unit corrected in *Table 38: NRST pin characteristics on page 67*. *Table 42: SPI characteristics on page 71* modified. I_{VREF} added to *Table 46: ADC characteristics on page 75*. *Table 48: ADC accuracy - limited test conditions* added. *Table 49: ADC accuracy* modified. LQFP100 package specifications updated (see *Section 6: Package information on page 80*). Recommended LQFP100, LQFP 64, LQFP48 and VFQFPN36 footprints added (see *Figure 55*, *Figure 60*, *Figure 64* and *Figure 44*). *Section 6.9: Thermal characteristics on page 105* modified, *Section 6.9.1* and *Section 6.9.2* added. *Appendix A: Important notes on page 81* removed.
21-Mar-2008	6	Small text changes. *Figure 11: Memory map* clarified. In *Table :*: – N_{END} tested over the whole temperature range – cycling conditions specified for t_{RET} – t_{RET} min modified at T_A = 55 °C V_{25}, Avg_Slope and T_L modified in *Table 50: TS characteristics*. CRC feature removed.
22-May-2008	7	CRC feature added back. Small text changes. *Section 1: Introduction* modified. *Section 2.2: Full compatibility throughout the family* added. I_{DD} at T_A max = 105 °C added to *Table 16: Typical and maximum current consumptions in Stop and Standby modes on page 45*. I_{DD_VBAT} removed from *Table 21: Typical current consumption in Standby mode on page 47*. Values added to *Table 41: SCL frequency (fPCLK1= 36 MHz.,VDD_I2C = 3.3 V) on page 70*. *Figure 33: SPI timing diagram - slave mode and CPHA = 0 on page 72* modified. *Equation 1* corrected. t_{RET} at T_A = 105 °C modified in *Table : on page 58*. V_{USB} added to *Table 44: USB DC electrical characteristics on page 74*. *Figure 65: LQFP100 PD max vs. TA on page 107* modified. Axx option added to *Table 63: Ordering information scheme on page 108*.

Table 64. Document revision history (continued)

Date	Revision	Changes
14-May-2013	15 (continued)	Updated *Figure 53: UFBGA100 - 100-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package outline* and *Table 56: UFBGA100 - 100-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package mechanical data* Updated *Figure 47: LFBGA100 - 100-ball low-profile fine pitch ball grid array, 10 x10 mm, 0.8 mm pitch, package outline* and *Table 53: LFBGA100 – 100-ball low-profile fine pitch ball grid array, 10 x 10 mm, 0.8 mm pitch, package mechanical data* Updated *Figure 60: TFBGA64 - 8 x 8 active ball array, 5 x 5 mm, 0.5 mm pitch, package outline* and *Table 59: TFBGA64 - 8 x 8 active ball array, 5 x 5 mm, 0.5 mm pitch, package mechanical data*
05-Aug-2013	16	Updated the reference for '$V_{ESD(CDM)}$' in *Table 32: ESD absolute maximum ratings* Corrected 'tf(IO)out' in *Figure 30: I/O AC characteristics definition* Updated *Table 52: UFQFPN48 - 48-lead, 7x7 mm, 0.5 mm pitch, ultra thin fine pitch quad flat package mechanical data*
21-Aug-2015	17	Updated *Table 3: STM32F103xx family* removing the note. Updated *Table 63: Ordering information scheme* removing the note. Updated *Section 6: Package information* and added *Section : Marking of engineering samples* for all packages. Updated I2C characteristics, added t_{SP} parameter and note 4 in *Table 40: I2C characteristics*. Updated *Figure 32: I2C bus AC waveforms and measurement circuit* swapping SCLL and SCLH. Updated *Figure 33: SPI timing diagram - slave mode and CPHA = 0*. Updated min/max value notes replacing 'Guaranteed by design, not tested in production" by "guaranteed by design". Updated min/max value notes replacing 'based on characterization, not tested in production" by "Guaranteed based on test during characterization". Updated *Table 19: Peripheral current consumption*.